

2SB1123/2SD1623

High-Current Switching Applications

Applications

· Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- · Adoption of FBET, MBIT processes.
- · Low collector-to-emitter saturation voltage.
- · Large current capacity and wide ASO.
- · Fast switching speed.
- · Very small size making it easy to provide highdensity, small-sized hybrid IC's.

(): 2SB1123

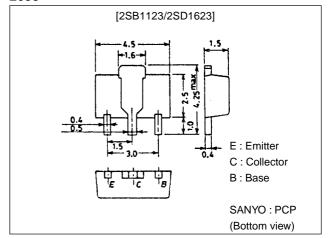
Specifications

Absolute Maximum Ratings at Ta = 25°C

Package Dimensions

unit:mm

2038



Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)60	V
Collector-to-Emitter Voltage	V _{CEO}		(–)50	V
Emitter-to-Base Voltage	V _{EBO}		(–)6	V
Collector Current	lС		(-)2	Α
Collector Current (Pulse)	I _{CP}		(-)4	Α
Collector Dissipation	PC		500	mW
		Mounted on ceramic board (250mm²×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Unit		
i didiffetei	Gymbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =(-)50V, I _E =0			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)100	nA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)100mA	100*		560*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)1.5A	40			
Gain-Bandwidth Product	fŢ	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz
Output Capacitance Cob		V _{CB} =(-)10V, f=1MHz		12		pF
				(22)		pF

 $\ensuremath{^*}$; The 2SB1123/2SD1623 are classified by 100mA $\ensuremath{h_{FE}}$ as follows :

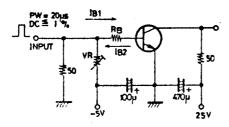
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Parameter	Symbol	Conditions	Ratings			Unit
Faiailletei	Symbol	Conditions	min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =(-)1A, I _B =(-)50mA		(-0.3)	(-0.7)	V
				0.15	0.4	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)1A, I _B =(-)50mA		(-)0.9	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)10μA, I _E =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)10μΑ, I _C =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit.		60		ns
				(60)		ns
Storage Time	t _{stg}	See specified Test Circuit.		550		ns
				(450)		ns
Fall Time	t _f	See specified Test Circuit.		30		ns
				(30)		ns

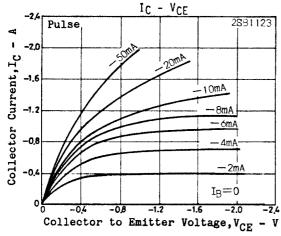
Switching Time Test Circuit

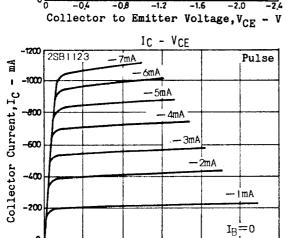


Marking: 2SB1123 -- BF 2SD1623 -- DF

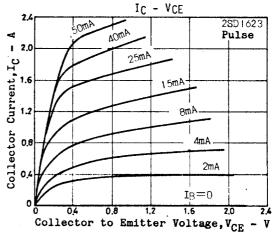
 $20I_{B1} = -20I_{B2} = I_{C} = 500mA$

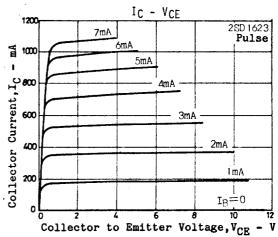
(For PNP, the polarity is reversed.) Unit (resistance: Ω , capacitance: F)

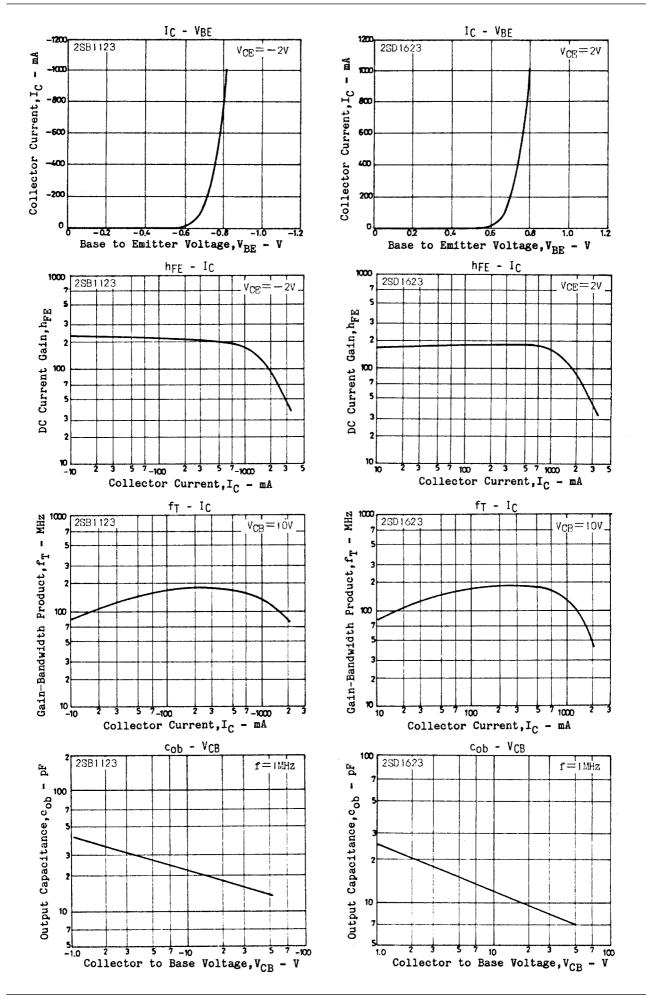




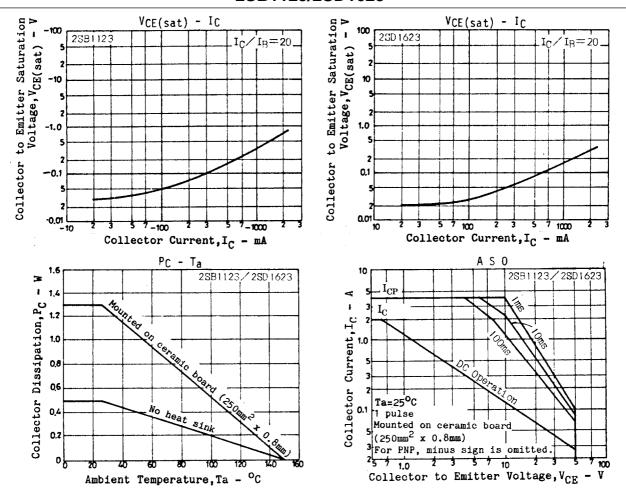
Collector to Emitter Voltage, VCE - V







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